Features

- Trench Power LV MOSFET Technology
- Moisture Sensitivity Level 3
- Halogen Free. “Green” Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

N-Channel Power MOSFET

Maximum Ratings

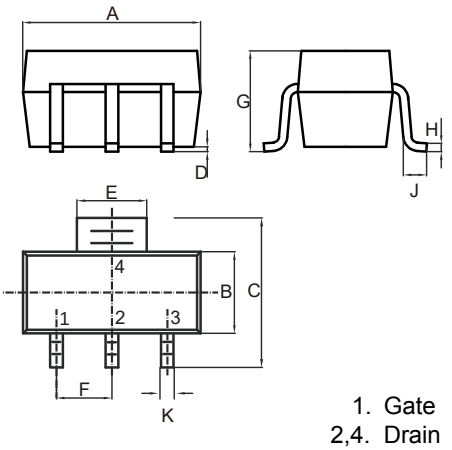
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance:64°C/W Junction to Ambient(Steady-State)(Note2)

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Volltage		V_{GS}	±20	V
Continuous Drain Current	T_a=25°C	I_D	4	A
	T_a=100°C		2.5	
Pulsed Drain Current(Note3)		I_{DM}	16	A
Single Pulsed Avalanche Energy(Note4)		P_D	2	W

Note:

1. Halogen free "Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C.
3. Repetitive rating; pulse width limited by max. junction temperature.
4. P_D is based on max. junction temperature, using junction to ambient thermal resistance.

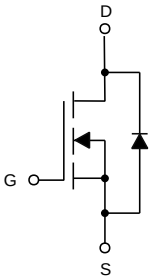
SOT-223

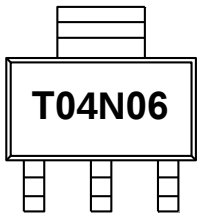


1. Gate
2,4. Drain
3. Source

DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.248	0.264	6.30	6.70	
B	0.130	0.146	3.30	3.70	
C	0.264	0.287	6.70	7.30	
D	0.001	0.004	0.02	0.10	
E	0.114	0.122	2.90	3.10	
F	0.091		2.30		TYP.
G	---	0.071	---	1.80	
H	0.009	0.014	0.23	0.35	
J	0.030	---	0.75	---	
K	0.026	0.033	0.66	0.84	

Internal Structure and Marking Code





Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=250μA	60			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} =60V, V_{GS} =0V			1	μA
Gate-Source Leakage Current	I_{GSS}	V_{DS} =0V, V_{GS} =±20V			±100	nA
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250μA	0.9	1.4	2	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=4A		68	88	mΩ
		V_{GS}=4.5V, I_D=3A		74	96	
Gate Resistance	R_g	F=1 MHz, Open drain		2.2		Ω
Diode Characteristics						
Continuous Body Diode Current	I_S				4	A
Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=2A			1.2	V
Reverse Recovery Time	t_{rr}	I_F=2A, dI_F/dt=100A/μs		21		ns
Reverse Recovery Charge	Q_{rr}			12		nC
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS}=30V,V_{GS}=0V,f=1MHz		501		pF
Output Capacitance	C_{oss}			26		
Reverse Transfer Capacitance	C_{rss}			21		
Total Gate Charge	Q_g	V_{DS}=30V,V_{GS}=10V, ID=2A		10.4		nC
Gate-Source Charge	Q_{gs}			1.3		
Gate-Drain Charge	Q_{gd}			2.4		
Turn-On Delay Time	$t_{d(on)}$	V_{DD}=30V, R_G=2.2Ω I_D=2A, V_{GS}=10V		2.3		ns
Turn-On Rise Time	t_r			13.4		
Turn-Off Delay Time	$t_{d(off)}$			15.6		
Turn-Off Fall Time	t_f			1.7		

Curve Characteristics

Fig. 1 - Typical Output Characteristics

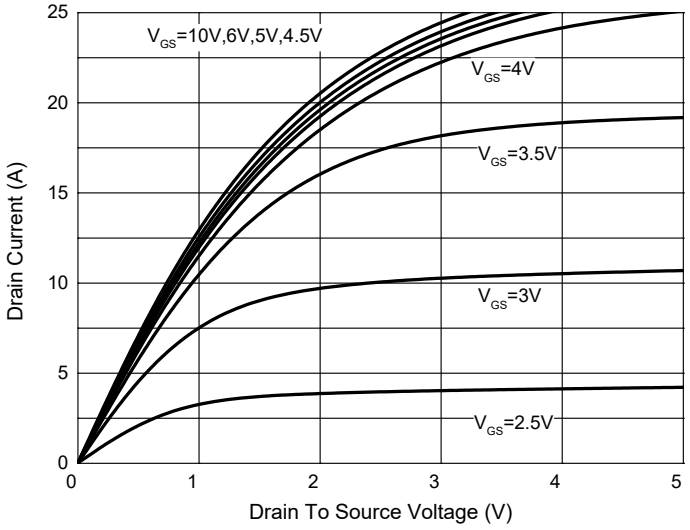


Fig. 2 - Transfer Characteristics

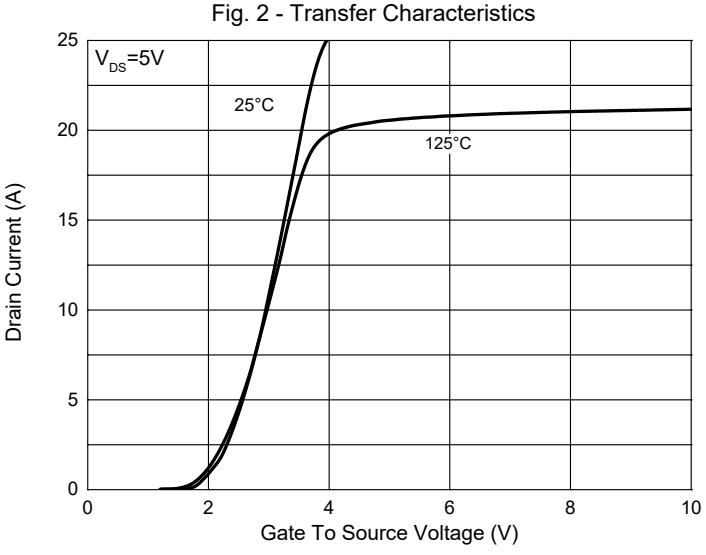


Fig. 3 - $R_{DS(ON)}$—V_{GS}

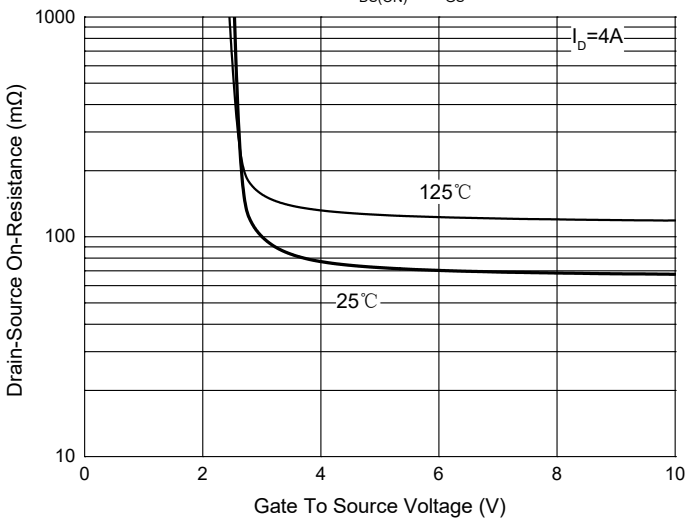


Fig. 4 - $R_{DS(ON)}$—I_D

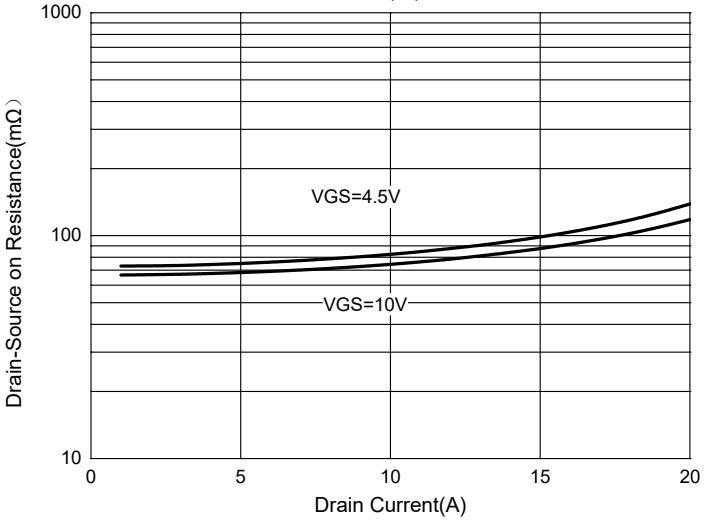


Fig. 5 - Capacitance Characteristics

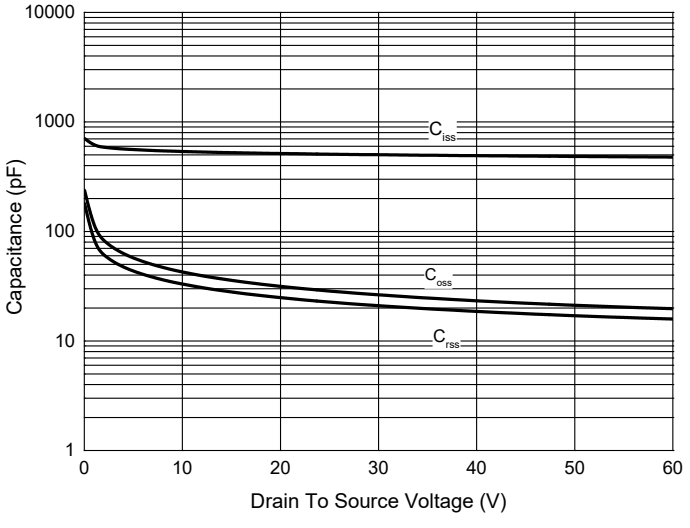
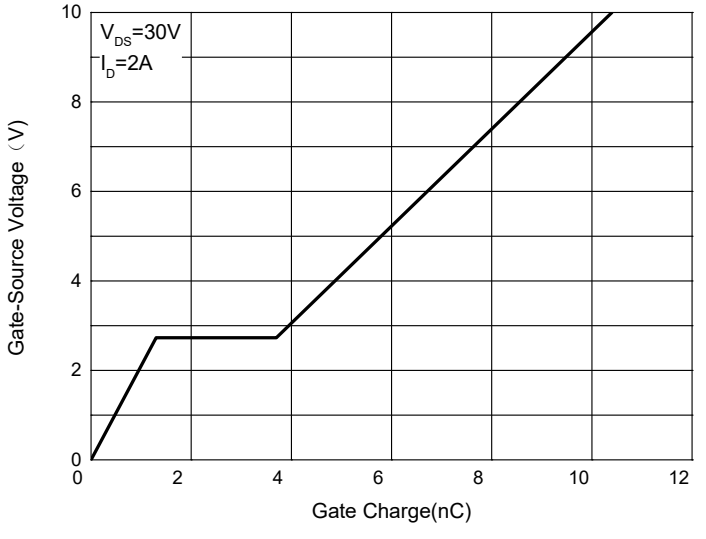


Fig. 6 - Gate Charge



Curve Characteristics

Fig. 7 - Nomalized Threshold Voltage

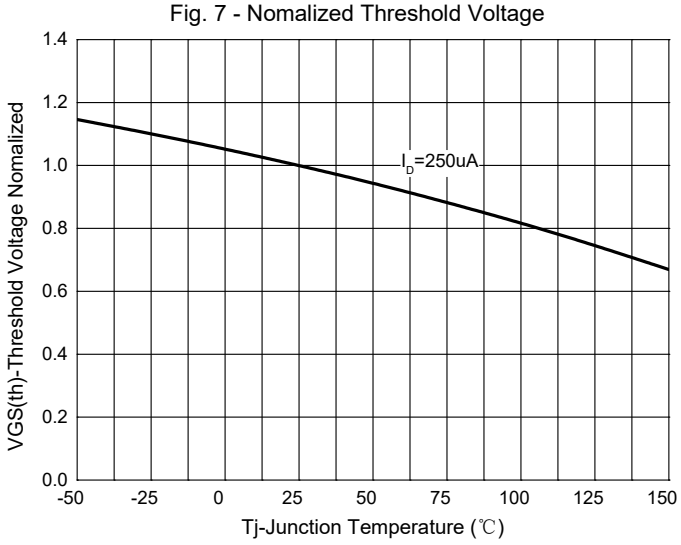


Fig.8-Normalized On Resistance Characteristics

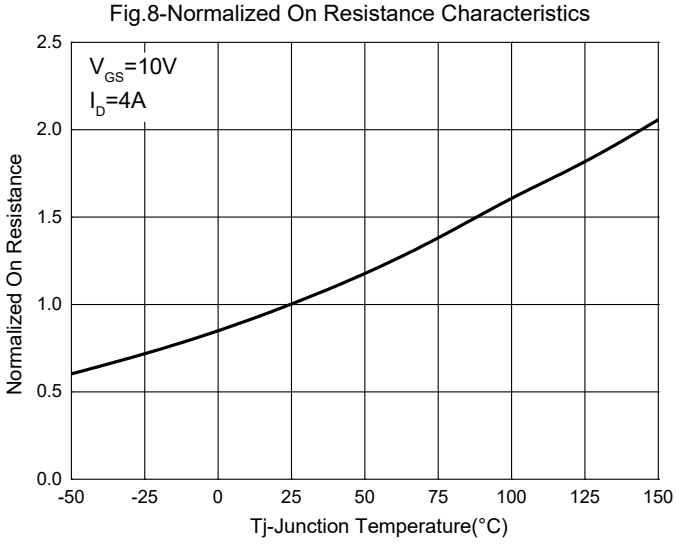


Fig.9 - I_S—V_{SD}

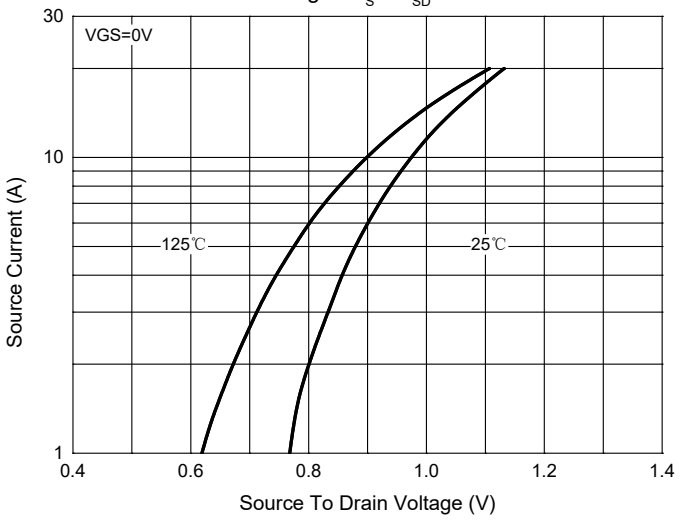


Fig. 10 - Drain Current

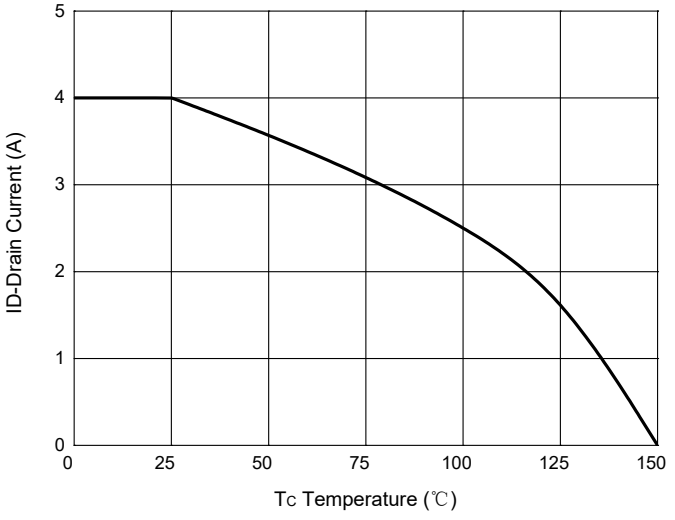
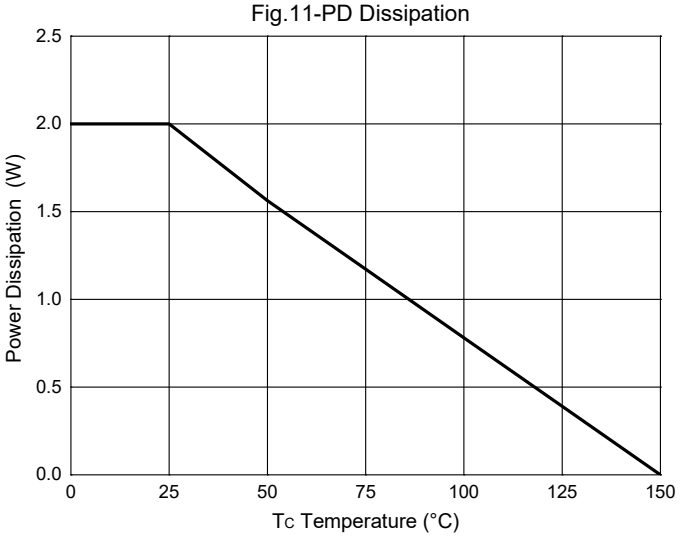


Fig.11-PD Dissipation



Curve Characteristics

Fig. 12 - Safe Operation Area

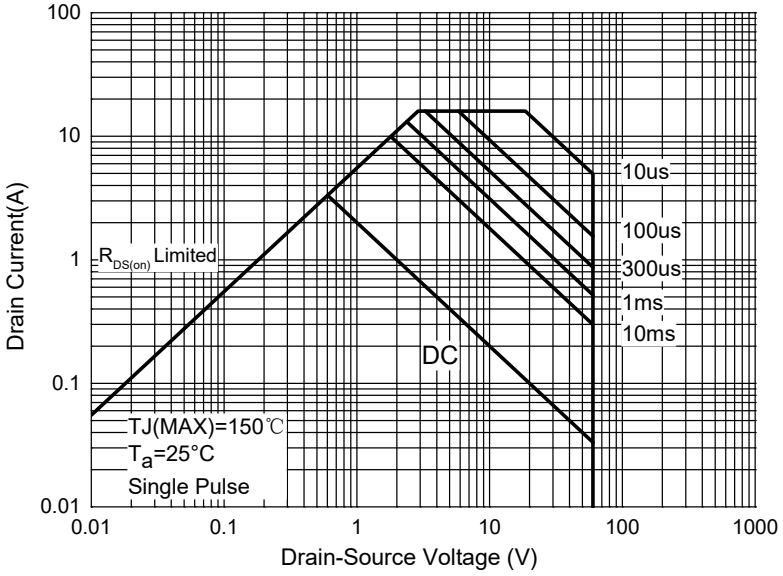
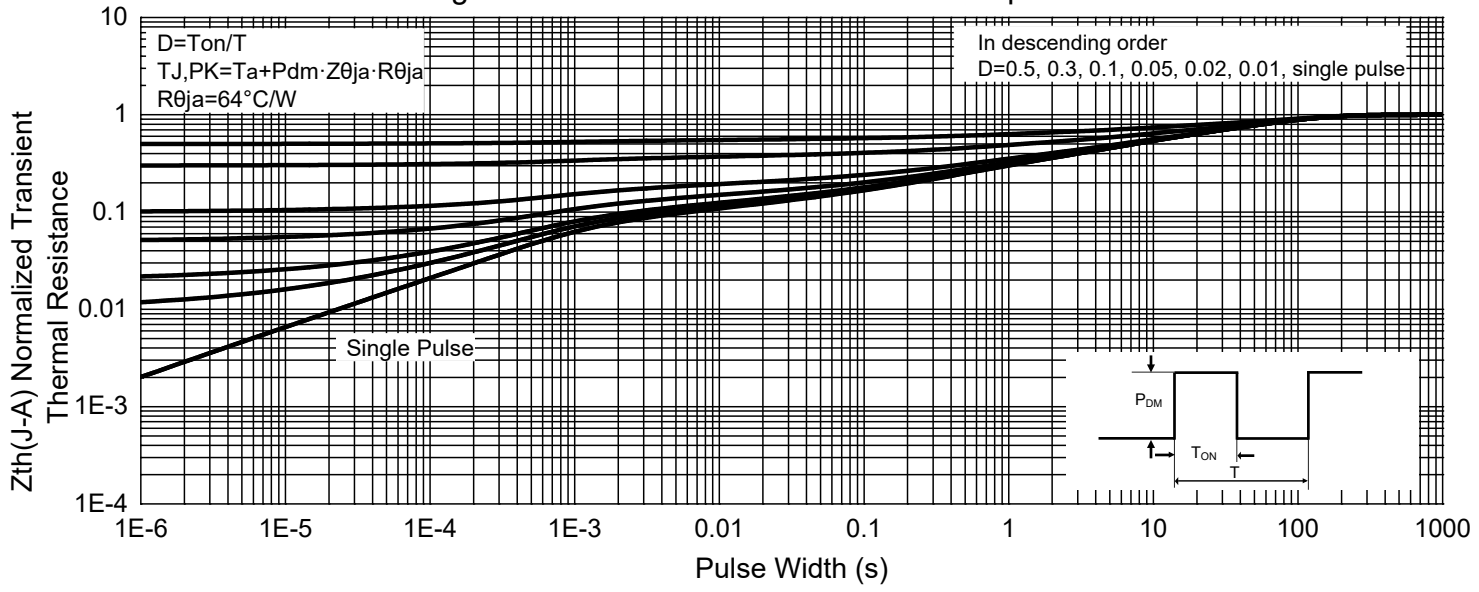


Fig. 13 -Normalized Transient Thermal Impedance



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 2.5Kpcs/Reel